



100V 175°C NPN LOW SAT MEDIUM POWER TRANSISTOR IN POWERDI5060-8

Features

- BV_{CEO} > 100V
- I_C = 3A Continuous Collector Current
- I_{CM} = 6A Peak Pulse Current
- $R_{CE(SAT)} < 150 m\Omega$
- Rated to +175°C—Ideal for High Ambient Temperature Environments
- Wettable Flank for Improved Optical Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DXTN3C100PSQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949;2016 certified facilities.

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Finish—Matte Tin Annealed Over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

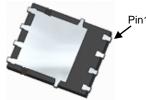
Applications

- Power Management
- Load Switch
- Linear Mode Voltage Regulator
- **Backlighting Applications**

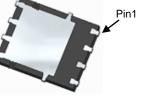
PowerDI5060-8 (SWP) (Type Q)



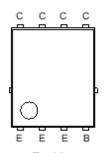
Top View



Bottom View



Internal Schematic



Top View Pin Configuration

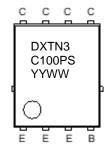
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTN3C100PSQ-13	Automotive	DXTN3C100PS	13	12	2500

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



DXTN3 = Product Type Marking Code C100PS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



Absolute Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	7	V
Base Current	lΒ	500	mA
Continuous Collector Current	lc	3	A
Peak Pulse Collector Current	Ісм	6	Α

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation (Note 5)		P _D	2.5	W	
Thermal Besistance, Junation to Ambient	(Note 5)	D	60	°C/M	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	140	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		R ₀ JL	5.7	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C		

ESD Ratings (Note 8)

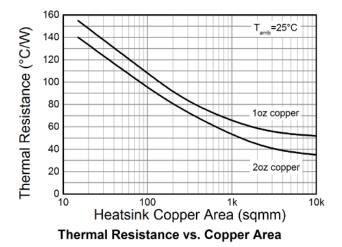
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

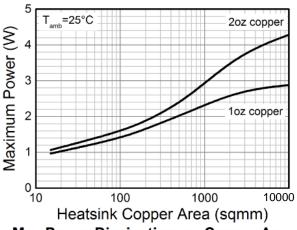
Notes:

- 5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except mounted on minimum recommended pad layout.
 7. Thermal resistance from junction to solder point (at the collector tab).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

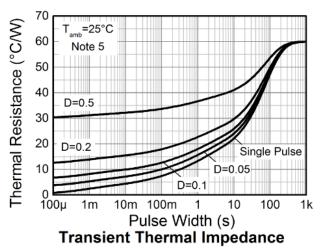


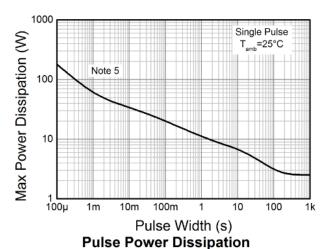
Typical Thermal Characteristics (@TA = +25°C, unless otherwise specified.)











3.0 Max Power Dissipation (W) Note 5 2.5 2.0 1.5 Note 6 0.5 0.0 50 75 25 100 125 150 Temperature (°C)



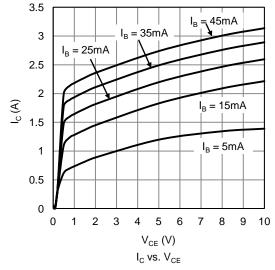
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

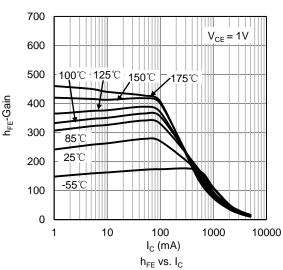
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV _{CBO}	100		_	V	I _C = 100μA	
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	100		_	V	I _C = 10mA	
Emitter-Base Breakdown Voltage	BV _{EBO}	7		_	V	I _E = 100μA	
Collector-Base Cutoff Current		_		100	nA	V _{CB} = 80V	
Collector-Base Cutoff Current	I _{CBO}	_		50	μΑ	V _{CB} = 80V @ T _J = +150°C	
Emitter Cutoff Current	I _{EBO}	_	1	100	nA	V _{EB} = 7V	
Collector-Emitter Cutoff Current	I _{CES}	_	1	100	nA	V _{CES} = 80V	
ON CHARACTERISTICS (Note 9)							
		150	250	_		$I_C = 500 \text{mA}, V_{CE} = 10 \text{V}$	
DC Current Gain	h	80	250	1		I _C = 1A, V _{CE} = 10V	
DC Current Gain	h _{FE}	20	100	_	_	$I_C = 2A, V_{CE} = 10V$	
		10	40	_		I _C = 3A, V _{CE} = 10V	
Collector Emitter Seturation Voltage	V	_	90	150	mV	$I_C = 1A$, $I_B = 50mA$	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	225	330	mV	$I_C = 3A$, $I_B = 300mA$	
Collector-Emitter Saturation Resistance	R _{CE(SAT)}	_	90	150	mΩ	$I_C = 1A$, $I_B = 50mA$	
Base-Emitter Saturation Voltage	V	_	0.86	1.0	V	$I_C = 1A$, $I_B = 50mA$	
Base-Emilier Saturation Voltage	V _{BE(SAT)}	_	1.0	1.2		$I_C = 2A$, $I_B = 200mA$	
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	0.67	0.85	V	I _C = 0.1A, V _{CE} = 2V	
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product	f⊤	_	140	_	MHz	$V_{CE} = 10V, I_{C} = 100mA, f = 100MHz$	
Output Capacitance	C _{obo}	_	11	1	pF	V _{CB} = 10V, f = 1MHz	
Delay Time	t _d	_	20	1	ns		
Rise Time	t _r	_	300	1	ns	$V_{CC} = 12.5V, I_C = 1A$ $I_{B1} = -I_{B2} = 0.05A$	
Turn-On Time	t _(on)	_	320	_	ns		
Storage Time	ts	_	830		ns		
Fall Time	t _f	_	470	_	ns		
Turn-Off Time	t _(off)	_	1300	_	ns		

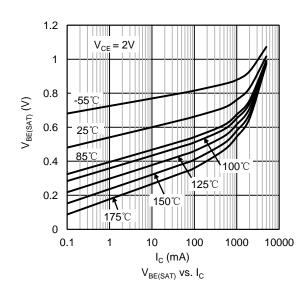
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

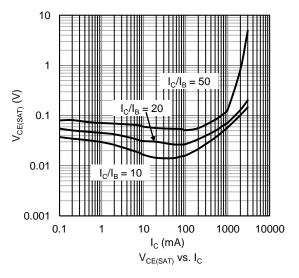


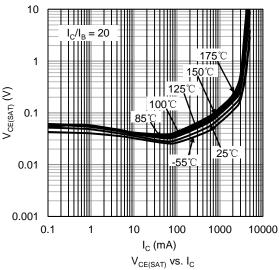
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

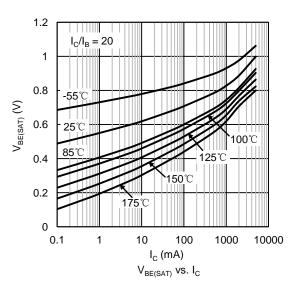














Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q) 1.900 1.900 DITAIL A DETAIL A DETAIL A

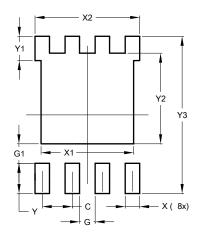
PowerDI5060-8 (SWP)						
	(Type Q)					
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A 1	0	0.05	_			
þ	0.30	0.50	0.41			
b2	0.20	0.35	0.25			
b4).25REF	-			
С	0.230	0.330	0.277			
D		.15 BS(
D1	4.70	5.10	4.90			
D2	3.56	3.96	3.76			
D2a	3.78	4.18	3.98			
Е	6	.40 BS0	\sim			
E1	5.60	6.00	5.80			
E2	3.46	3.86	3.66			
E2a	4.195	4.595	4.395			
е	1.27BSC					
k	1.05	_	_			
L	0.635	0.835	0.735			
La	0.635	0.835	0.735			
L1	0.200	0.400	0.300			
L1a	0.050REF					
L4	0.025	0.225	0.125			
М	3.205	4.005	3.605			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

Suggested Pad Layout

L1a(8x)

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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